



Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I ² C, IrDA, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	56
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 20x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-FQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk22dx256vlk5

Table of Contents

1 Ordering parts.....	3	5.4.1 Thermal operating requirements.....	21
1.1 Determining valid orderable parts.....	3	5.4.2 Thermal attributes.....	21
2 Part identification.....	3	6 Peripheral operating requirements and behaviors.....	22
2.1 Description.....	3	6.1 Core modules.....	22
2.2 Format.....	3	6.1.1 JTAG electricals.....	22
2.3 Fields.....	3	6.2 System modules.....	25
2.4 Example.....	4	6.3 Clock modules.....	25
2.5 Small package marking.....	4	6.3.1 MCG specifications.....	25
3 Terminology and guidelines.....	5	6.3.2 Oscillator electrical specifications.....	27
3.1 Definition: Operating requirement.....	5	6.3.3 32 kHz oscillator electrical characteristics.....	30
3.2 Definition: Operating behavior.....	5	6.4 Memories and memory interfaces.....	30
3.3 Definition: Attribute.....	6	6.4.1 Flash electrical specifications.....	30
3.4 Definition: Rating.....	6	6.4.2 EzPort switching specifications.....	33
3.5 Result of exceeding a rating.....	7	6.5 Security and integrity modules.....	34
3.6 Relationship between ratings and operating requirements.....	7	6.6 Analog.....	34
3.7 Guidelines for ratings and operating requirements.....	8	6.6.1 ADC electrical specifications.....	35
3.8 Definition: Typical value.....	8	6.6.2 CMP and 6-bit DAC electrical specifications.....	39
3.9 Typical value conditions.....	9	6.6.3 12-bit DAC electrical characteristics.....	41
4 Ratings.....	9	6.6.4 Voltage reference electrical specifications.....	44
4.1 Thermal handling ratings.....	9	6.7 Timers.....	45
4.2 Moisture handling ratings.....	10	6.8 Communication interfaces.....	45
4.3 ESD handling ratings.....	10	6.8.1 USB electrical specifications.....	45
4.4 Voltage and current operating ratings.....	10	6.8.2 USB DCD electrical specifications.....	46
5 General.....	10	6.8.3 VREG electrical specifications.....	46
5.1 AC electrical characteristics.....	11	6.8.4 DSPI switching specifications (limited voltage range).....	47
5.2 Nonswitching electrical specifications.....	11	6.8.5 DSPI switching specifications (full voltage range).....	48
5.2.1 Voltage and current operating requirements.....	11	6.8.6 I2C switching specifications.....	50
5.2.2 LVD and POR operating requirements.....	12	6.8.7 UART switching specifications.....	50
5.2.3 Voltage and current operating behaviors.....	13	6.8.8 Normal Run, Wait and Stop mode performance over the full operating voltage range.....	50
5.2.4 Power mode transition operating behaviors.....	13	6.8.9 VLPR, VLPW, and VLPS mode performance over the full operating voltage range.....	52
5.2.5 Power consumption operating behaviors.....	14	7 Dimensions.....	54
5.2.6 EMC radiated emissions operating behaviors.....	18	7.1 Obtaining package dimensions.....	54
5.2.7 Designing with radiated emissions in mind.....	19	8 Pinout.....	54
5.2.8 Capacitance attributes.....	19	8.1 K22 Signal Multiplexing and Pin Assignments.....	54
5.3 Switching specifications.....	19	8.2 K22 Pinouts.....	58
5.3.1 Device clock specifications.....	19	9 Revision History.....	59
5.3.2 General switching specifications.....	20		
5.4 Thermal specifications.....	21		

1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to freescale.com and perform a part number search for the following device numbers: PK22 and MK22 .

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

Q K## A M FFF R T PP CC N

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	- M = Fully qualified, general market flow - P = Prequalification
K##	Kinetis family	K22
A	Key attribute	- D = Cortex-M4 w/ DSP - F = Cortex-M4 w/ DSP and FPU
M	Flash memory type	- N = Program flash only - X = Program flash and FlexMemory

Table continues on the next page...

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior:

Symbol	Description	Min.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10	130	μA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
I_{Ccont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins - Negative current injection - Positive current injection	-25 —	— +25	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

- All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is less than V_{AIO_MIN} or greater than V_{AIO_MAX} , a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO_MIN}-V_{IN})/|I_{ICAIO}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO_MAX})/|I_{ICAIO}|$. Select the larger of these two calculated resistances if the pin is exposed to positive and negative injection currents.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
V_{LVW1H}	Low-voltage warning thresholds — high range Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	1
V_{LVW2H}	Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	80	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
V_{LVW1L}	Low-voltage warning thresholds — low range Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	1
V_{LVW2L}	Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μ s	

1. Rising threshold is the sum of falling threshold and hysteresis voltage

Table 3. VBAT power operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{POR_VBAT}	Falling VBAT supply POR detect voltage	0.8	1.1	1.5	V	

5.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{OH}	Output high voltage — high drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OH} = -9\text{ mA}$	$V_{DD} - 0.5$	—	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OH} = -3\text{ mA}$	$V_{DD} - 0.5$	—	V	
	Output high voltage — low drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OH} = -2\text{ mA}$	$V_{DD} - 0.5$	—	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OH} = -0.6\text{ mA}$	$V_{DD} - 0.5$	—	V	
I _{OHT}	Output high current total for all ports	—	100	mA	
V _{OL}	Output low voltage — high drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OL} = 9\text{ mA}$	—	0.5	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OL} = 3\text{ mA}$	—	0.5	V	
	Output low voltage — low drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OL} = 2\text{ mA}$	—	0.5	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OL} = 0.6\text{ mA}$	—	0.5	V	
I _{OLT}	Output low current total for all ports	—	100	mA	
I _{IN}	Input leakage current (per pin)				
	• @ full temperature range	—	1.0	μA	1
	• @ 25 °C	—	0.1	μA	
I _{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	
I _{OZ}	Total Hi-Z (off-state) leakage current (all input pins)	—	4	μA	
R _{PU}	Internal pullup resistors	22	50	kΩ	2
R _{PD}	Internal pulldown resistors	22	50	kΩ	3

1. Tested by ganged leakage method
2. Measured at V_{input} = V_{SS}
3. Measured at V_{input} = V_{DD}

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I _{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V • @ -40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	1.03 1.92 4.03 17.43	1.8 7.5 15.9 28.7	μA	
I _{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit enabled • @ -40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.543 1.36 3.39 16.52	1.1 7.58 14.3 24.1	μA	
I _{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit disabled • @ -40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.359 1.03 2.87 15.20	0.95 6.8 15.4 25.3	μA	
I _{DD_VBAT}	Average current when CPU is not accessing RTC registers at 3.0 V • @ -40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.91 1.1 1.5 4.3	1.1 1.35 1.85 5.7	μA	9

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. 50 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FEI mode. All peripheral clocks disabled.
3. 50 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FEI mode. All peripheral clocks enabled, and peripherals are in active operation.
4. Max values are measured with CPU executing DSP instructions
5. 25 MHz core and system clock, 25 MHz bus clock, and 12.5 MHz flash clock. MCG configured for FEI mode.
6. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash.
7. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled but peripherals are not in active operation. Code executing from flash.
8. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled.
9. Includes 32 kHz oscillator current and RTC operation.

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode
- USB regulator disabled
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL

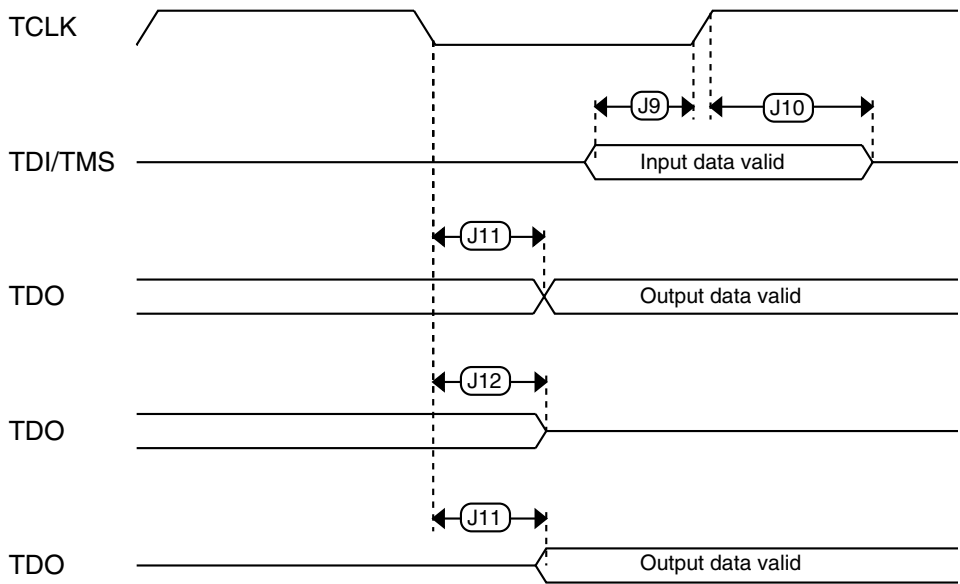


Figure 6. Test Access Port timing

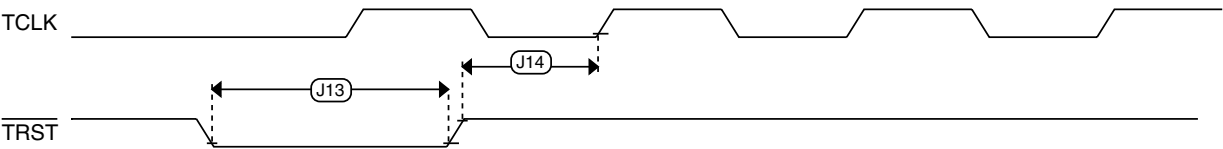


Figure 7. $\overline{\text{TRST}}$ timing

6.2 System modules

There are no specifications necessary for the device's system modules.

6.3 Clock modules

Table 14. MCG specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
J_{cyc_fll}	FLL period jitter $f_{DCO} = 48 \text{ MHz}$ $f_{DCO} = 98 \text{ MHz}$	—	180	—	ps	
$t_{fll_acquire}$	FLL target frequency acquisition time	—	—	1	ms	7
PLL						
f_{vco}	VCO operating frequency	48.0	—	100	MHz	
I_{pll}	PLL operating current PLL @ 96 MHz ($f_{osc_hi_1} = 8 \text{ MHz}$, $f_{pll_ref} = 2 \text{ MHz}$, VDIV multiplier = 48)	—	1060	—	μA	8
I_{pll}	PLL operating current PLL @ 48 MHz ($f_{osc_hi_1} = 8 \text{ MHz}$, $f_{pll_ref} = 2 \text{ MHz}$, VDIV multiplier = 24)	—	600	—	μA	8
f_{pll_ref}	PLL reference frequency range	2.0	—	4.0	MHz	
J_{cyc_pll}	PLL period jitter (RMS) $f_{vco} = 48 \text{ MHz}$ $f_{vco} = 100 \text{ MHz}$	—	120	—	ps	9
J_{acc_pll}	PLL accumulated jitter over 1 μs (RMS) $f_{vco} = 48 \text{ MHz}$ $f_{vco} = 100 \text{ MHz}$	—	1350	—	ps	9
D_{lock}	Lock entry frequency tolerance	± 1.49	—	± 2.98	%	
D_{unl}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%	
t_{pll_lock}	Lock detector detection time	—	—	$150 \times 10^{-6} + 1075(1/f_{pll_ref})$	s	10

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. $2 \text{ V} \leq \text{VDD} \leq 3.6 \text{ V}$.
3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
4. The resulting system clock frequencies should not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature should be considered.
5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
7. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
8. Excludes any oscillator currents that are also consuming power while PLL is in operation.
9. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
10. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

6.3.2 Oscillator electrical specifications

6.3.2.1 Oscillator DC electrical specifications

Table 15. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 4 MHz	—	200	—	μ A	
	• 8 MHz (RANGE=01)	—	300	—	μ A	
	• 16 MHz	—	950	—	μ A	
	• 24 MHz	—	1.2	—	mA	
	• 32 MHz	—	1.5	—	mA	
I_{DDOSC}	Supply current — high-gain mode (HGO=1)					1
	• 32 kHz	—	25	—	μ A	
	• 4 MHz	—	400	—	μ A	
	• 8 MHz (RANGE=01)	—	500	—	μ A	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	M Ω	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	M Ω	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	M Ω	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	M Ω	
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	k Ω	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	k Ω	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	k Ω	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	k Ω	

Table continues on the next page...

Table 20. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{swapx01}	Swap Control execution time	—	200	—	μs	
t_{swapx02}	• control code 0x01	—	70	150	μs	
t_{swapx04}	• control code 0x02	—	70	150	μs	
t_{swapx08}	• control code 0x04	—	—	30	μs	
$t_{\text{pgmpart64k}}$	Program Partition for EEPROM execution time	—	138	—	ms	
	• 64 KB FlexNVM					
t_{setramff}	Set FlexRAM Function execution time:	—	70	—	μs	
$t_{\text{setram32k}}$	• Control Code 0xFF	—	0.8	1.2	ms	
$t_{\text{setram64k}}$	• 32 KB EEPROM backup	—	1.3	1.9	ms	
	• 64 KB EEPROM backup					
Byte-write to FlexRAM for EEPROM operation						
$t_{\text{eewr8bers}}$	Byte-write to erased FlexRAM location execution time	—	175	260	μs	3
$t_{\text{eewr8b32k}}$	Byte-write to FlexRAM execution time:	—	385	1800	μs	
$t_{\text{eewr8b64k}}$	• 32 KB EEPROM backup		475	2000	μs	
	• 64 KB EEPROM backup					
Word-write to FlexRAM for EEPROM operation						
$t_{\text{eewr16bers}}$	Word-write to erased FlexRAM location execution time	—	175	260	μs	
$t_{\text{eewr16b32k}}$	Word-write to FlexRAM execution time:	—	385	1800	μs	
$t_{\text{eewr16b64k}}$	• 32 KB EEPROM backup	—	475	2000	μs	
	• 64 KB EEPROM backup					
Longword-write to FlexRAM for EEPROM operation						
$t_{\text{eewr32bers}}$	Longword-write to erased FlexRAM location execution time	—	360	540	μs	
$t_{\text{eewr32b32k}}$	Longword-write to FlexRAM execution time:	—	630	2050	μs	
$t_{\text{eewr32b64k}}$	• 32 KB EEPROM backup	—	810	2250	μs	
	• 64 KB EEPROM backup					

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

6.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in [Table 24](#) and [Table 25](#) are achievable on the differential pins ADCx_DP0, ADCx_DM0.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

6.6.1.1 16-bit ADC operating conditions

Table 24. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V _{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV _{DDA}	Supply voltage	Delta to V _{DD} (V _{DD} – V _{DDA})	-100	0	+100	mV	2
ΔV _{SSA}	Ground voltage	Delta to V _{SS} (V _{SS} – V _{SSA})	-100	0	+100	mV	2
V _{REFH}	ADC reference voltage high		1.13	V _{DDA}	V _{DDA}	V	
V _{REFL}	ADC reference voltage low		V _{SSA}	V _{SSA}	V _{SSA}	V	
V _{ADIN}	Input voltage	16-bit differential mode - All other modes	V _{REFL} V _{REFL}	— —	31/32 * V _{REFH} V _{REFH}	V	
C _{ADIN}	Input capacitance	16-bit mode 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	
R _{ADIN}	Input resistance		—	2	5	kΩ	
R _{AS}	Analog source resistance	13-bit / 12-bit modes f _{ADCK} < 4 MHz	—	—	5	kΩ	3
f _{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	18.0	MHz	4
f _{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C _{rate}	ADC conversion rate	≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	5
C _{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	Ksps	5

Typical ADC 16-bit Single-Ended ENOB vs ADC Clock
100Hz, 90% FS Sine Input

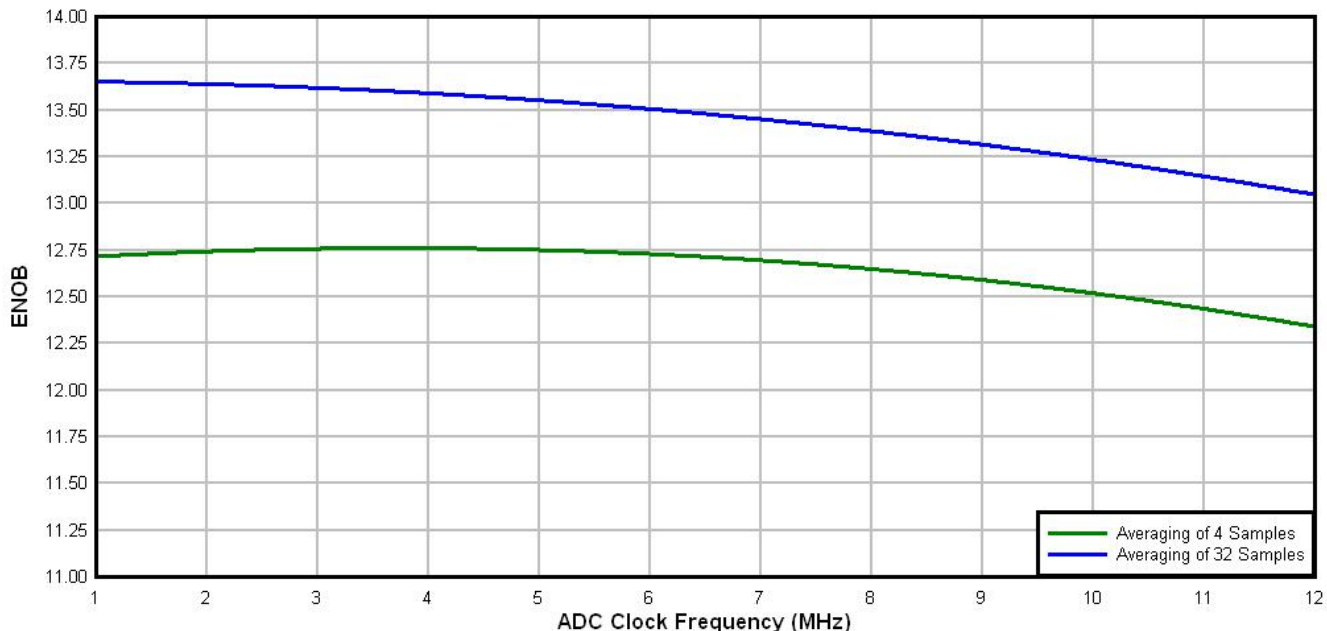


Figure 11. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

6.6.2 CMP and 6-bit DAC electrical specifications

Table 26. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μ A
I_{DDLs}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μ A
V_{AIN}	Analog input voltage	$V_{SS} - 0.3$	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis ¹ - CR0[HYSTCTR] = 00 - CR0[HYSTCTR] = 01 - CR0[HYSTCTR] = 10 - CR0[HYSTCTR] = 11	—	5 10 20 30	—	mV mV mV mV
V_{CMPOH}	Output high	$V_{DD} - 0.5$	—	—	V
V_{CMPOI}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay ²	—	—	40	μ s

Table continues on the next page...

6.6.3.2 12-bit DAC operating behaviors

Table 28. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	330	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	1200	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFFF	$V_{DACR} - 100$	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	± 8	LSB	2
DNL	Differential non-linearity error — $V_{DACR} > 2 V$	—	—	± 1	LSB	3
DNL	Differential non-linearity error — $V_{DACR} = V_{REF_OUT}$	—	—	± 1	LSB	4
V_{OFFSET}	Offset error	—	± 0.4	± 0.8	%FSR	5
E_G	Gain error	—	± 0.1	± 0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \geq 2.4 V$	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	$\mu V/C$	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
R_{op}	Output resistance (load = 3 k Ω)	—	—	250	Ω	
SR	Slew rate -80h → F7Fh → 80h - High power (SP_{HP}) - Low power (SP_{LP})	1.2 0.05	1.7 0.12	— —	V/ μs	
CT	Channel to channel cross talk	—	—	-80	dB	
BW	3dB bandwidth - High power (SP_{HP}) - Low power (SP_{LP})	550 40	— —	— —	kHz	

- Settling within ± 1 LSB
- The INL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV
- The DNL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV
- The DNL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV with $V_{DDA} > 2.4 V$
- Calculated by a best fit curve from $V_{SS} + 100$ mV to $V_{DACR} - 100$ mV
- $V_{DDA} = 3.0 V$, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

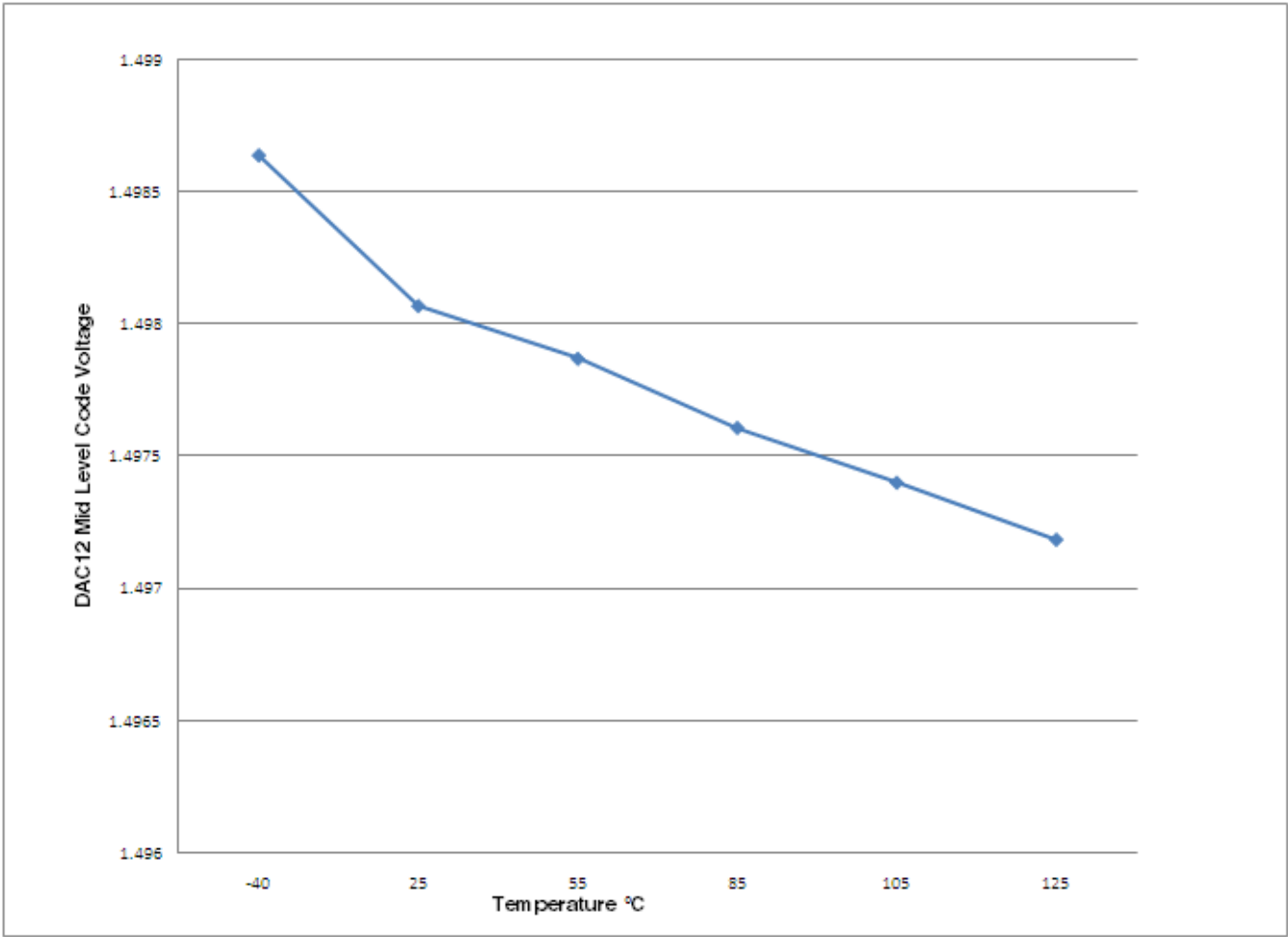


Figure 15. Offset at half scale vs. temperature

6.6.4 Voltage reference electrical specifications

Table 29. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V _{DDA}	Supply voltage	1.71	3.6	V	
T _A	Temperature	Operating temperature range of the device		°C	
C _L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

6.8.1 USB electrical specifications

The USB electricals for the USB On-the-Go module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit usb.org.

6.8.2 USB DCD electrical specifications

Table 33. USB DCD electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V _{DP_SRC}	USB_DP source voltage (up to 250 μ A)	0.5	—	0.7	V
V _{LGC}	Threshold voltage for logic high	0.8	—	2.0	V
I _{DP_SRC}	USB_DP source current	7	10	13	μ A
I _{DM_SINK}	USB_DM sink current	50	100	150	μ A
R _{DM_DWN}	D- pulldown resistance for data pin contact detect	14.25	—	24.8	k Ω
V _{DAT_REF}	Data detect voltage	0.25	0.33	0.4	V

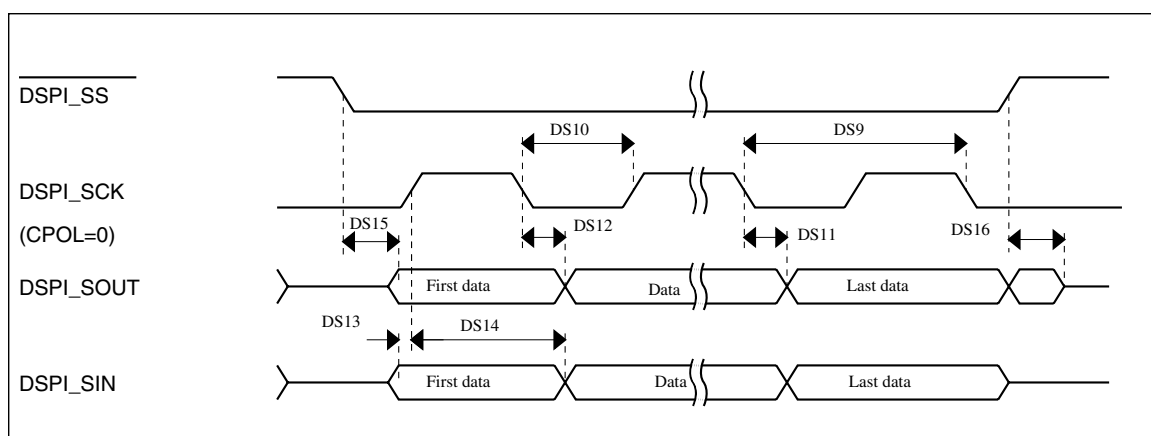
6.8.3 VREG electrical specifications

Table 34. VREG electrical specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
V _{REGIN}	Input supply voltage	2.7	—	5.5	V	
I _{DDon}	Quiescent current — Run mode, load current equal zero, input supply (V _{REGIN}) > 3.6 V	—	125	186	μ A	
I _{DDstby}	Quiescent current — Standby mode, load current equal zero	—	1.1	10	μ A	
I _{DDoff}	Quiescent current — Shutdown mode - V_{REGIN} = 5.0 V and temperature=25 $^{\circ}$C - Across operating voltage and temperature	—	650	—	nA	
		—	—	4	μ A	
I _{LOADstby}	Maximum load current — Standby mode	—	—	1	mA	
V _{Reg33out}	Regulator output voltage — Input supply (V _{REGIN}) > 3.6 V - Run mode - Standby mode	3	3.3	3.6	V	
		2.1	2.8	3.6	V	
V _{Reg33out}	Regulator output voltage — Input supply (V _{REGIN}) < 3.6 V, pass-through mode	2.1	—	3.6	V	2
C _{OUT}	External output capacitor	1.76	2.2	8.16	μ F	
ESR	External output capacitor equivalent series resistance	1	—	100	m Ω	
I _{LIM}	Short circuit current	—	315	—	mA	

Table 36. Slave mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation		12.5	MHz
DS9	DSPI_SCK input cycle time	$4 \times t_{BUS}$	—	ns
DS10	DSPI_SCK input high/low time	$(t_{SCK}/2) - 2$	$(t_{SCK}/2) + 2$	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	10	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	DSPI_SS active to DSPI_SOUT driven	—	14	ns
DS16	DSPI_SS inactive to DSPI_SOUT not driven	—	14	ns


Figure 17. DSPI classic SPI timing — slave mode

6.8.5 DSPI switching specifications (full voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provides DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 37. Master mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	1
	Frequency of operation	—	12.5	MHz	
DS1	DSPI_SCK output cycle time	$4 \times t_{BUS}$	—	ns	

Table continues on the next page...

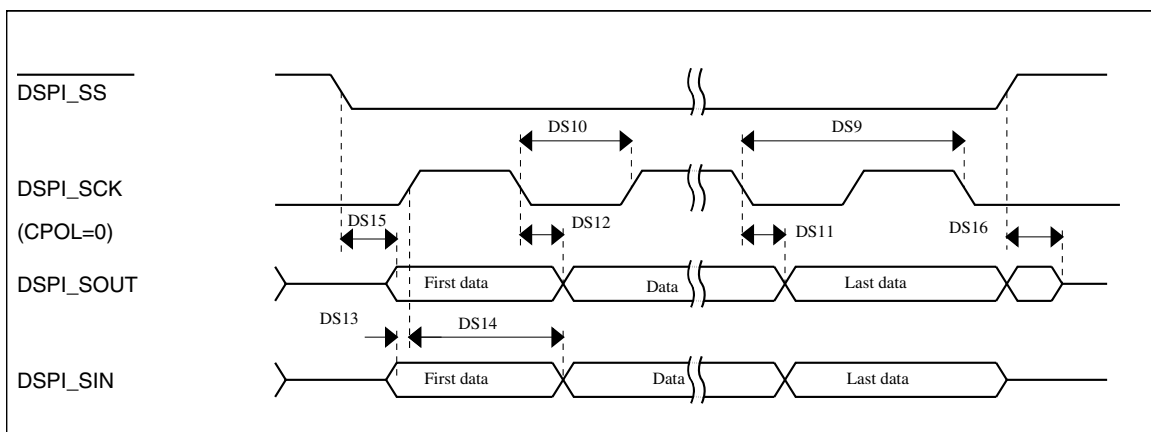


Figure 19. DSPI classic SPI timing — slave mode

6.8.6 I²C switching specifications

See [General switching specifications](#).

6.8.7 UART switching specifications

See [General switching specifications](#).

6.8.8 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

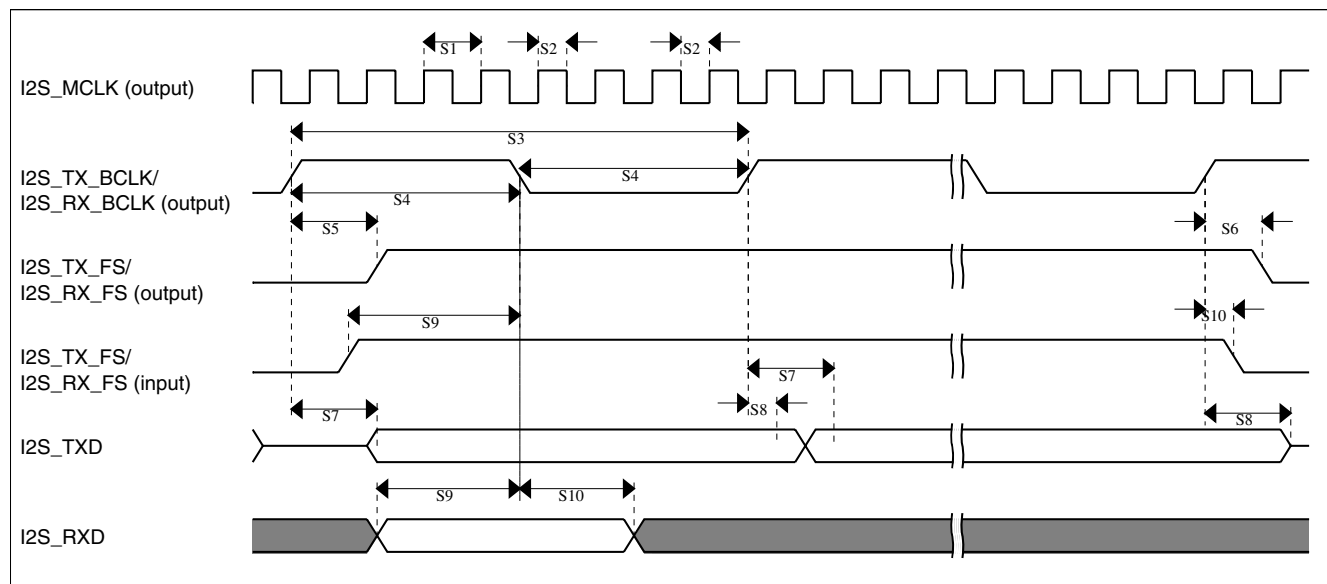
Table 39. I2S/SAI master mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK (as an input) pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns

Table continues on the next page...

Table 39. I2S/SAI master mode timing (continued)

Num.	Characteristic	Min.	Max.	Unit
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	25	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns


Figure 20. I2S/SAI timing — master modes
Table 40. I2S/SAI slave mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	80	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	10	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	29	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	10	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid ¹	—	21	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

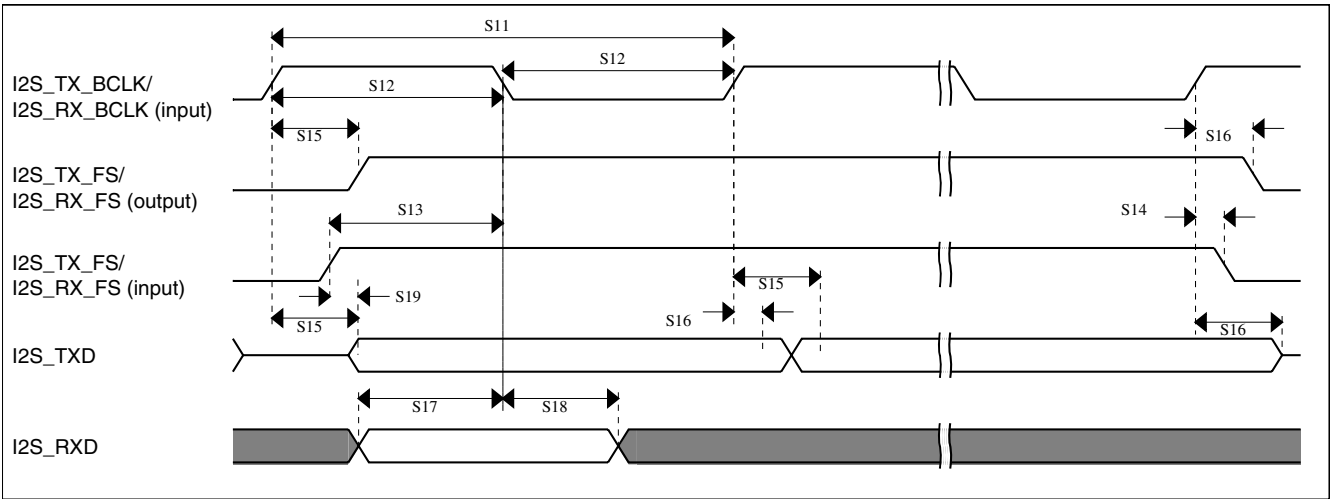


Figure 23. I2S/SAI timing — slave modes

7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
80-pin LQFP	98ASS23174W

8 Pinout

8.1 K22 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

NOTE

- The analog input signals ADC0_SE10, ADC0_SE11, ADC0_DP1, and ADC0_DM1 are available only for K11,

How to Reach Us:**Home Page:**

freescale.com

Web Support:

freescale.com/support

Information in this document is provided solely to enable system and software implementers to use Freescale products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits based on the information in this document.

Freescale reserves the right to make changes without further notice to any products herein. Freescale makes no warranty, representation, or guarantee regarding the suitability of its products for any particular purpose, nor does Freescale assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters that may be provided in Freescale data sheets and/or specifications can and do vary in different applications, and actual performance may vary over time. All operating parameters, including "typicals," must be validated for each customer application by customer's technical experts. Freescale does not convey any license under its patent rights nor the rights of others. Freescale sells products pursuant to standard terms and conditions of sale, which can be found at the following address: freescale.com/SalesTermsandConditions.

Freescale, the Freescale logo, Energy Efficient Solutions logo, and Kinetis are trademarks of Freescale Semiconductor, Inc., Reg. U.S. Pat. & Tm. Off. All other product or service names are the property of their respective owners. ARM and Cortex are the registered trademarks of ARM Limited.

© 2012-2013 Freescale Semiconductor, Inc.